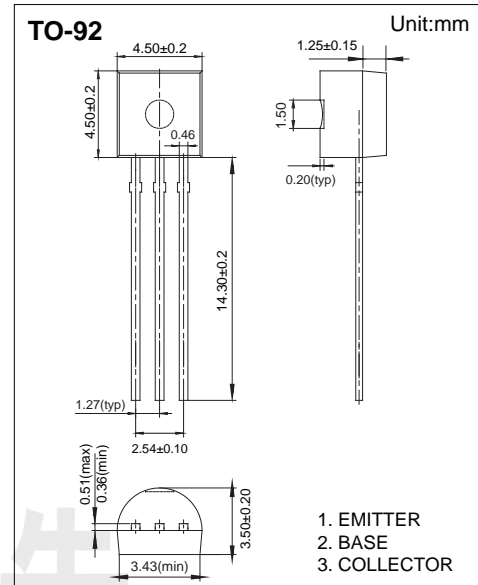


Transistor

PNP Transistors SS8550

■ Features

- High Total Power Dissipation. ($P_C=1W$)
- Collector current: $I_C=-1.5A$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-40	V
Collector - Emitter Voltage	V_{CE0}	-25	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-1.5	A
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collecto- base breakdown voltage	V_{CB0}	$I_C = -100 \mu A, I_E = 0$	-40			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -0.1 mA, I_B = 0$	-25			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu A, I_C = 0$	-5			
Collector cut-off current	I_{CBO}	$V_{CB} = -40 V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{CEO}	$V_{CE} = -20 V, I_E = 0$			-0.1	
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 V, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800 mA, I_B = -80 mA$			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800 mA, I_B = -80 mA$			-1.2	
Base-emitter voltage	$V_{BE(on)}$	$V_{CE} = -1 V, I_C = -10 mA$			-1	
DC current gain	$h_{FE(1)}$	$V_{CE} = -1 V, I_C = -100 mA$	85		400	
	$h_{FE(2)}$	$V_{CE} = -1 V, I_C = -800 mA$	40			
Out capacitance	C_{ob}	$V_{CB} = -10 V, I_E = 0 mA, f = 1 MHz$			20	pF
Transition frequency	f_T	$V_{CE} = -5 V, I_C = -10 mA, f = 30 MHz$	100			MHz

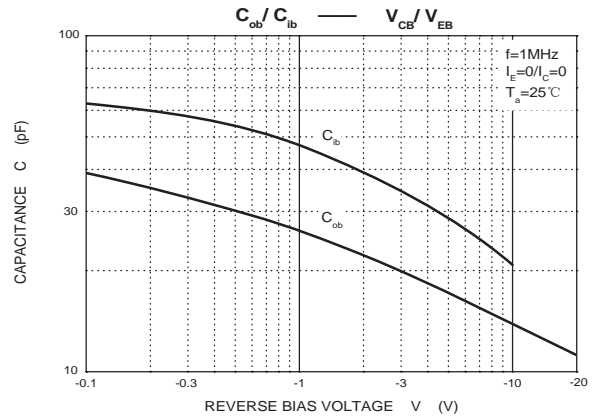
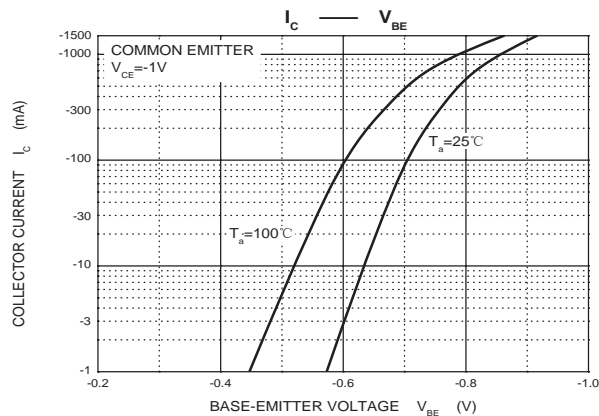
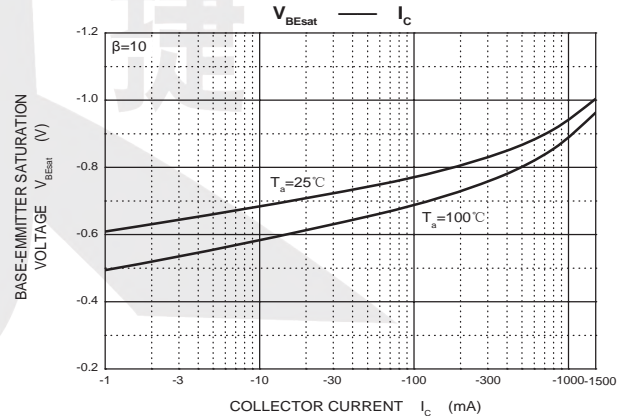
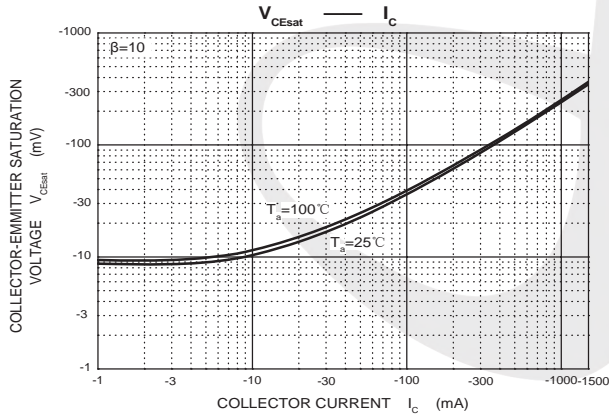
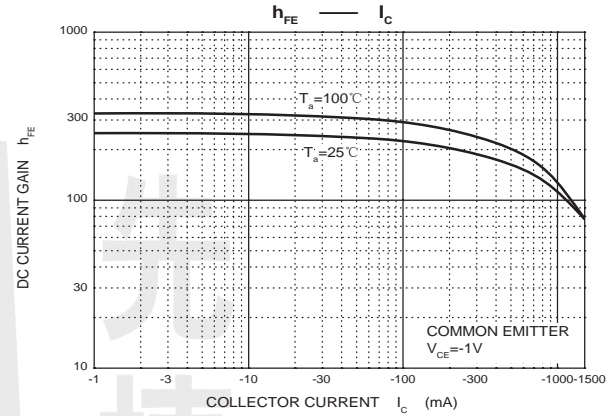
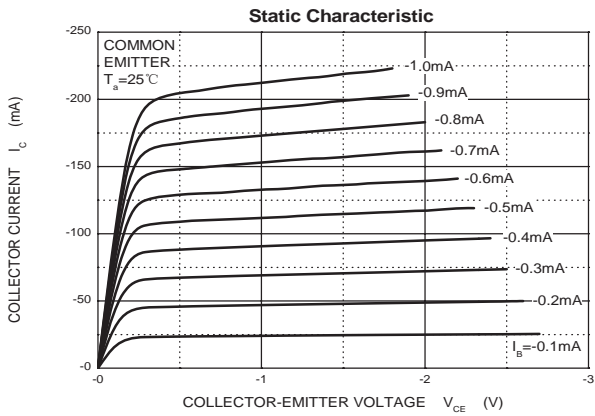
Transistor

PNP Transistors SS8550

Classification of hFE(1)

Rank	B	C	D	D3
Range	85-160	120-200	160-300	300-400

Typical Characteristics



Transistor

PNP Transistors SS8550

■ Typical Characteristics

